

1. (Twice amended) A method of generating ions, comprising:

heating an ion source material composed of indium monoiodide (InI) at a temperature of not lower than 250°C and not higher than 380°C to produce a desired ion beam current effective to generate vapor of said indium monoiodide (InI); and generating indium (In) ions by discharging said vapor.

--21. (New) The method according to claim 1, wherein said heating an ion

source material comprises heating said indium monoiodide (InI) at a temperature of not lower than 300°C and not higher than 380°C to produce said desired ion beam current effective to generate said vapor of said indium monoiodide (InI).

22. (New) A method of generating ions, comprising:

heating an ion source material composed of indium monoiodide (InI), to generate vapor of said indium monoiodide (InI); and

generating indium (In) ions by discharging said vapor in an arc chamber, wherein a filament is provided on one side surface of said arc chamber, and a reflecting counter electrode is provided on a second side surface of said arc chamber opposite to said one side surface.

23. (New) A method of generating ions, comprising:

heating an ion source material composed of indium monoiodide (InI), to generate vapor of said indium monoiodide (InI); and

generating indium (In) ions by discharging said vapor in an arc chamber, wherein two gas inlets for an inert gas and said vapor are provided on a same face of the arc chamber and are configured to introduce said inert gas and said vapor into said chamber in one direction.--

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